Application Number:	10	10849617					
Filing Date:	20-	20-May-2004					
Title of Invention:		METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING REGROWN OHMIC CONTACT REGIONS					
First Named Inventor/Applicant Name:	Ad	Adam William Saxler					
Filer:	Eliz	Elizabeth A. Stanek/Candi Riggs					
Attorney Docket Number:	530	5308-413					
Filed as Large Entity	•						
Utility under 35 USC 111(a) Filing Fees							
Description		Fee Code	Quantity	Amount	Sub-Total ir USD(\$)		
Basic Filing:			'				
Pages:							
Claims:							
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							

Publ. Fee- early, voluntary, or normal

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
	Total in USD (\$)			1740